

CMLD6263

**SURFACE MOUNT SILICON  
DUAL, ISOLATED  
HIGH VOLTAGE  
SCHOTTKY DIODE**

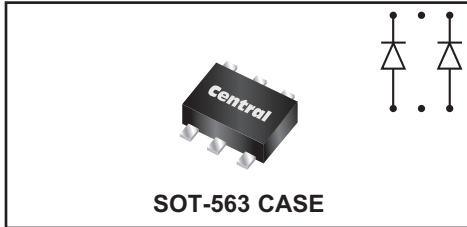


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**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLD6263 incorporates two galvanically isolated, high voltage, low  $V_F$  silicon diodes in a space saving SOT-563 surface mount package. These diodes are designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: 63D or 63**



**SOT-563 CASE**

**FEATURES:**

- High Voltage (70V)
- Low Forward Voltage
- Galvanically Isolated

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Peak Repetitive Reverse Voltage	$V_{RRM}$	70	V
Continuous Forward Current	$I_F$	15	mA
Peak Forward Surge Current, $t_p=1.0\text{s}$	$I_{FSM}$	50	mA
Power Dissipation	$P_D$	250	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	500	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
$I_R$	$V_R=50\text{V}$		98	200	nA
$BV_R$	$I_R=10\mu\text{A}$	70			V
$V_F$	$I_F=1.0\text{mA}$		395	410	mV
$C_J$	$V_R=0, f=1.0\text{MHz}$			2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns